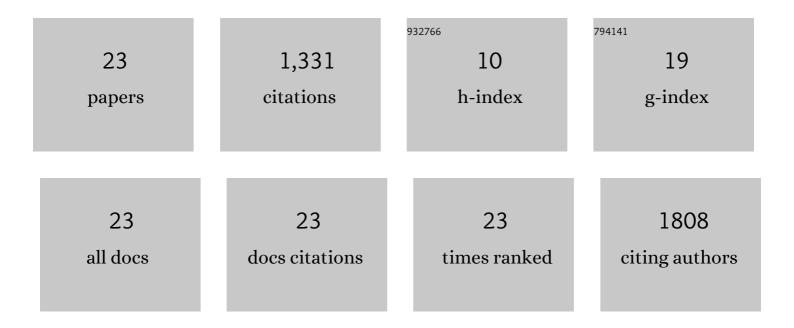
Andrew D Koehler

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Ultrawideâ€Bandgap Semiconductors: Research Opportunities and Challenges. Advanced Electronic Materials, 2018, 4, 1600501.	2.6	839
2	Vertical GaN Junction Barrier Schottky Rectifiers by Selective Ion Implantation. IEEE Electron Device Letters, 2017, 38, 1097-1100.	2.2	136
3	Substrate-Dependent Effects on the Response of AlGaN/GaN HEMTs to 2-MeV Proton Irradiation. IEEE Electron Device Letters, 2014, 35, 826-828.	2.2	78
4	GaN-On-Diamond HEMT Technology With T _{AVG} = 176°C at P _{DC,max} = 56 W/mm Measured by Transient Thermoreflectance Imaging. IEEE Electron Device Letters, 2019, 40, 881-884.	2.2	52
5	Vertical GaN Junction Barrier Schottky Diodes. ECS Journal of Solid State Science and Technology, 2017, 6, Q10-Q12.	0.9	33
6	High resistivity halide vapor phase homoepitaxial β-Ga2O3 films co-doped by silicon and nitrogen. Applied Physics Letters, 2018, 113, .	1.5	30
7	A Comparison of Single-Event Transients in Pristine and Irradiated <formula formulatype="inline"><tex notation="TeX">\${{m A}_{0.3}}{{m Ga}_{0.7}}{{m N}/{m GaN}}</tex> HEMTs using Two-Photon Absorption and Heavy Ions. IEEE Transactions on Nuclear Science, 2015, 62, 2743-2751.</formula 	1.2	22
8	Spatial Mapping of Pristine and Irradiated AlGaN/GaN HEMTs With UV Single-Photon Absorption Single-Event Transient Technique. IEEE Transactions on Nuclear Science, 2016, 63, 1995-2001.	1.2	20
9	Degradation of dynamic ON-resistance of AlGaN/GaN HEMTs under proton irradiation. , 2013, , .		14
10	Electrothermal Evaluation of AlGaN/GaN Membrane High Electron Mobility Transistors by Transient Thermoreflectance. IEEE Journal of the Electron Devices Society, 2018, 6, 922-930.	1.2	14
11	High Voltage GaN Lateral Photoconductive Semiconductor Switches. ECS Journal of Solid State Science and Technology, 2017, 6, S3099-S3102.	0.9	12
12	Hyperspectral Electroluminescence Characterization of OFF-State Device Characteristics in Proton Irradiated High Voltage AlGaN/GaN HEMTs. ECS Journal of Solid State Science and Technology, 2016, 5, Q289-Q293.	0.9	11
13	A Tri-Layer PECVD SiN Passivation Process for Improved AlGaN/GaN HEMT Performance. ECS Journal of Solid State Science and Technology, 2017, 6, P58-P61.	0.9	10
14	The Effect of the Gate-Connected Field Plate on Single-Event Transients in AlGaN/GaN Schottky-Gate HEMTs. IEEE Transactions on Nuclear Science, 2019, 66, 1682-1687.	1.2	10
15	Degradation mechanisms of AlGaN/GaN HEMTs on sapphire, Si, and SiC substrates under proton irradiation. , 2014, , .		9
16	Application of a Focused, Pulsed X-Ray Beam to the Investigation of Single-Event Transients in Al _{0.3} Ga _{0.7} N/GaN HEMTs. IEEE Transactions on Nuclear Science, 2017, 64, 97-105.	1.2	9
17	Investigation of Single-Event Transients in AlGaN/GaN MIS-Gate HEMTs Using a Focused X-Ray Beam. IEEE Transactions on Nuclear Science, 2019, 66, 368-375.	1.2	9
18	Effect of GaN Substrate Properties on Vertical GaN PiN Diode Electrical Performance. Journal of Electronic Materials, 2021, 50, 3013-3021.	1.0	8

#	Article	IF	CITATIONS
19	Correlation of the Spatial Variation of Single-Event Transient Sensitivity With Thermoreflectance Thermography in \${ext {Al}}_{x} {ext {Ga}}_{1-x}\$ N/GaN HEMTs. IEEE Transactions on Nuclear Science, 2018, 65, 369-375.	1.2	6
20	A Study on the Impact of Mid-Gap Defects on Vertical GaN Diodes. IEEE Transactions on Semiconductor Manufacturing, 2020, 33, 546-551.	1.4	5
21	Reduced Contact Resistance in GaN Using Selective Area Si Ion Implantation. IEEE Transactions on Semiconductor Manufacturing, 2019, 32, 478-482.	1.4	3
22	Vertical power devices enabled by bulk GaN substrates. , 2019, , .		1
23	Vertical GaN junction barrier schottky diodes by Mg implantation and activation annealing. , 2016, , .		Ο